



SIE822DF-T1-E3 Information



For Reference Only

Part NumberSIE822DF-T1-E3ManufacturerVishay Siliconix

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 20V 50A 10-POLARPAK

Package 10-PolarPAK? (S)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









SIE822DF-T1-E3 Specifications

Manufacturer Part Number SIE822DF-T1-E3 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 10-PolarPAK? (S) Series TrenchFET? FET Type N-Channel Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Add On (Max) @ Id, Vgs Add On (Max) @ Id, Vgs Suffine Max) Suffice Max Suffice Max Suffice Max Suffice Mount Supplier Device Package Package / Case 10-PolarPAK? (S)	Manufacturer Part Number	SIE822DF-T1-E3
Package 10-PolarPAK? (S) Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 50A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 78nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4200pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 5.2W (Ta), 104W (Tc) Rds On (Max) @ Id, Vgs 3.4 mOhm @ 18.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (S) Package / Case 10-PolarPAK? (S)	Manufacturer	Vishay Siliconix
Package 10-PolarPAK? (S) Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 50A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 78nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4200pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 5.2W (Ta), 104W (Tc) Rds On (Max) @ Id, Vgs 3.4 mOhm @ 18.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (S) Package / Case 10-PolarPAK? (S)	Category	Discrete Semiconductor Products
Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 50A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 78nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4200pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 5.2W (Ta), 104W (Tc) Rds On (Max) @ Id, Vgs 3.4 mOhm @ 18.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (S) Package / Case 10-PolarPAK? (S)		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C50A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs78nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4200pF @ 10VVgs (Max)±20VFET Feature-Power Dissipation (Max)5.2W (Ta), 104W (Tc)Rds On (Max) @ Id, Vgs3.4 mOhm @ 18.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package10-PolarPAK? (S)Package / Case10-PolarPAK? (S)	Package	10-PolarPAK? (S)
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C50A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs78nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4200pF @ 10VVgs (Max)±20VFET Feature-Power Dissipation (Max)5.2W (Ta), 104W (Tc)Rds On (Max) @ Id, Vgs3.4 mOhm @ 18.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package10-PolarPAK? (S)Package / Case10-PolarPAK? (S)	Series	TrenchFET?
Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C50A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs78nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4200pF @ 10VVgs (Max)±20VFET Feature-Power Dissipation (Max)5.2W (Ta), 104W (Tc)Rds On (Max) @ Id, Vgs3.4 mOhm @ 18.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package10-PolarPAK? (S)Package / Case10-PolarPAK? (S)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Tanc @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.4 mOhm @ 18.3A, 10V Operating Temperature Supplier Device Package Package / Case 50A (Tc) 50A (T	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs78nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4200pF @ 10VVgs (Max)±20VFET Feature-Power Dissipation (Max)5.2W (Ta), 104W (Tc)Rds On (Max) @ Id, Vgs3.4 mOhm @ 18.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package10-PolarPAK? (S)Package / Case10-PolarPAK? (S)	Drain to Source Voltage (Vdss)	20V
Vgs(th) (Max) @ Id 3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 78nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4200pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 5.2W (Ta), 104W (Tc) Rds On (Max) @ Id, Vgs 3.4 mOhm @ 18.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (S) Package / Case 10-PolarPAK? (S)	Current - Continuous Drain (Id) @ 25°C	50A (Tc)
Gate Charge (Qg) (Max) @ Vgs 78nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4200pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 5.2W (Ta), 104W (Tc) Rds On (Max) @ Id, Vgs 3.4 mOhm @ 18.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (S) Package / Case 10-PolarPAK? (S)	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.4 mOhm @ 18.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (S) Package / Case	Vgs(th) (Max) @ Id	3V @ 250μA
Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 5.2W (Ta), 104W (Tc) Rds On (Max) @ Id, Vgs 3.4 mOhm @ 18.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (S) Package / Case 10-PolarPAK? (S)	Gate Charge (Qg) (Max) @ Vgs	78nC @ 10V
FET Feature - Power Dissipation (Max) 5.2W (Ta), 104W (Tc) Rds On (Max) @ Id, Vgs 3.4 mOhm @ 18.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (S) Package / Case 10-PolarPAK? (S)	Input Capacitance (Ciss) (Max) @ Vds	4200pF @ 10V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.4 mOhm @ 18.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (S) Package / Case 10-PolarPAK? (S)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs3.4 mOhm @ 18.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package10-PolarPAK? (S)Package / Case10-PolarPAK? (S)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (S) Package / Case 10-PolarPAK? (S)	Power Dissipation (Max)	5.2W (Ta), 104W (Tc)
Mounting Type Surface Mount Supplier Device Package 10-PolarPAK? (S) Package / Case 10-PolarPAK? (S)	Rds On (Max) @ Id, Vgs	3.4 mOhm @ 18.3A, 10V
Supplier Device Package 10-PolarPAK? (S) Package / Case 10-PolarPAK? (S)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 10-PolarPAK? (S)	Mounting Type	Surface Mount
,,	Supplier Device Package	10-PolarPAK? (S)
Report errors?	Package / Case	10-PolarPAK? (S)
		Report errors?

SIE822DF-T1-E3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SIE822DF-T1-E3 Payment Methods





















SIE822DF-T1-E3 Shipping Methods













If you have any question about SIE822DF-T1-E3, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com